Roy G Gordon

List of Publications by Year
in descending order

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286	26,639	5876	6630
papers	citations	81 h-index	156 g-index

293	293	293	18598
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Criteria for Choosing Transparent Conductors. MRS Bulletin, 2000, 25, 52-57.	1.7	1,341
2	A metal-free organicâ€“inorganic aqueous flow battery. Nature, 2014, 505, 195-198.	13.7	1,333
3	Theory for the Forces between Closedâ€Shell Atoms and Molecules. Journal of Chemical Physics, 1972, 56, 3122-3133.	1.2	1,220
4	Alkaline quinone flow battery. Science, 2015, 349, 1529-1532.	6.0	833
5	New Method for Constructing Wavefunctions for Bound States and Scattering. Journal of Chemical Physics, 1969, 51, 14-25.	1.2	606
6	Atomic layer deposition of transition metals. Nature Materials, 2003, 2, 749-754.	13.3	592
7	Textured aluminumâ€doped zinc oxide thin films from atmospheric pressure chemicalâ€vapor deposition. Journal of Applied Physics, 1992, 71, 880-890.	1.1	581
8	Overcoming Efficiency Limitations of SnSâ€Based Solar Cells. Advanced Energy Materials, 2014, 4, 1400496.	10.2	508
9	Self-Aligned Ballistic Molecular Transistors and Electrically Parallel Nanotube Arrays. Nano Letters, 2004, 4, 1319-1322.	4.5	505
10	Carbon Nanotube Field-Effect Transistors with Integrated Ohmic Contacts and High-Î¹ Gate Dielectrics. Nano Letters, 2004, 4, 447-450.	4.5	498
11	Atomic Layer Deposition of Hafnium and Zirconium Oxides Using Metal Amide Precursors. Chemistry of Materials, 2002, 14, 4350-4358.	3.2	462
12	High Performance n-Type Carbon Nanotube Field-Effect Transistors with Chemically Doped Contacts. Nano Letters, 2005, 5, 345-348.	4.5	453
13	A redox-flow battery with an alloxazine-based organic electrolyte. Nature Energy, 2016, 1, .	19.8	427
14	A Neutral pH Aqueous Organicâ€“Organometallic Redox Flow Battery with Extremely High Capacity Retention. ACS Energy Letters, 2017, 2, 639-644.	8.8	418
15	Error Bounds in Equilibrium Statistical Mechanics. Journal of Mathematical Physics, 1968, 9, 655-663.	0.5	394
16	Atomic Layer Deposition to Fine-Tune the Surface Properties and Diameters of Fabricated Nanopores. Nano Letters, 2004, 4, 1333-1337.	4.5	385
17	Atomic Layer Deposition of Tin Monosulfide Thin Films. Advanced Energy Materials, 2011, 1, 1116-1125.	10.2	383
18	Quantum scattering theory of rotational relaxation and spectral line shapes in H2â€“He gas mixtures. Journal of Chemical Physics, 1973, 58, 5422-5443.	1.2	356

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19	Surface Chemistry and Electrical Properties of Germanium Nanowires. Journal of the American Chemical Society, 2004, 126, 11602-11611.	6.6	335
20	Alkaline Quinone Flow Battery with Long Lifetime at pH 12. Joule, 2018, 2, 1894-1906.	11.7	293
21	Enhancing the efficiency of SnS solar cells via band-offset engineering with a zinc oxysulfide buffer layer. Applied Physics Letters, 2013, 102, .	1.5	281
22	Surface morphology and crystallinity control in the atomic layer deposition (ALD) of hafnium and zirconium oxide thin films. Journal of Crystal Growth, 2003, 249, 251-261.	0.7	269
23	Synthesis and Characterization of Volatile, Thermally Stable, Reactive Transition Metal Amidinates. Inorganic Chemistry, 2003, 42, 7951-7958.	1.9	267
24	Textured fluorine-doped ZnO films by atmospheric pressure chemical vapor deposition and their use in amorphous silicon solar cells. Solar Cells, 1991, 30, 437-450.	0.6	266
25	Exact recursive evaluation of 3jâ€•and 6jâ€coefficients for quantumâ€mechanical coupling of angular momenta. Journal of Mathematical Physics, 1975, 16, 1961-1970.	0.5	247
26	Atmospheric pressure chemical vapor deposition of gallium doped zinc oxide thin films from diethyl zinc, water, and triethyl gallium. Journal of Applied Physics, 1992, 72, 5381-5392.	1.1	242
27	Atomic Layer Deposited Gallium Oxide Buffer Layer Enables 1.2 V Openâ€Circuit Voltage in Cuprous Oxide Solar Cells. Advanced Materials, 2014, 26, 4704-4710.	11.1	242
28	3.88% Efficient Tin Sulfide Solar Cells using Congruent Thermal Evaporation. Advanced Materials, 2014, 26, 7488-7492.	11.1	227
29	Improved Error Bounds for the Longâ€Range Forces between Atoms. Journal of Chemical Physics, 1971, 54, 663-673.	1.2	222
30	Rapid Vapor Deposition of Highly Conformal Silica Nanolaminates. Science, 2002, 298, 402-406.	6.0	217
31	Atomic Layer Deposition on Suspended Single-Walled Carbon Nanotubes via Gas-Phase Noncovalent Functionalization. Nano Letters, 2006, 6, 699-703.	4.5	212
32	Chemical vapor deposition of titanium, zirconium, and hafnium nitride thin films. Chemistry of Materials, 1991, 3, 1138-1148.	3.2	210
33	Scaled electron gas approximation for intermolecular forces. Journal of Chemical Physics, 1979, 71, 1325-1339.	1.2	198
34	A Long-Lifetime All-Organic Aqueous Flow Battery Utilizing TMAP-TEMPO Radical. CheM, 2019, 5, 1861-1870.	5.8	196
35	Atomic Layer Deposition of Ultrathin Copper Metal Films from a Liquid Copper(I) Amidinate Precursor. Journal of the Electrochemical Society, 2006, 153, C787.	1.3	194
36	A Phosphonateâ€Functionalized Quinone Redox Flow Battery at Nearâ€Neutral pH with Record Capacity Retention Rate. Advanced Energy Materials, 2019, 9, 1900039.	10.2	194

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37	Anthraquinone Derivatives in Aqueous Flow Batteries. Advanced Energy Materials, 2017, 7, 1601488.	10.2	189
38	ALD of Hafnium Oxide Thin Films from Tetrakis(ethylmethylamino)hafnium and Ozone. Journal of the Electrochemical Society, 2005, 152, G213.	1.3	176
39	Chemical vapor deposition of vanadium, niobium, and tantalum nitride thin films. Chemistry of Materials, 1993, 5, 614-619.	3.2	165
40	Alkaline Benzoquinone Aqueous Flow Battery for Largeâ€Scale Storage of Electrical Energy. Advanced Energy Materials, 2018, 8, 1702056.	10.2	161
41	Study of the electron gas approximation. Journal of Chemical Physics, 1974, 60, 1842-1850.	1.2	160
42	Ultrathin amorphous zinc-tin-oxide buffer layer for enhancing heterojunction interface quality in metal-oxide solar cells. Energy and Environmental Science, 2013, 6, 2112.	15.6	160
43	A Water-Miscible Quinone Flow Battery with High Volumetric Capacity and Energy Density. ACS Energy Letters, 2019, 4, 1342-1348.	8.8	154
44	On a semiclassical study of molecular collisions. II. Application to HClâ€argon. Journal of Chemical Physics, 1973, 58, 4149-4170.	1.2	153
45	Synthesis and Characterization of Copper(I) Amidinates as Precursors for Atomic Layer Deposition (ALD) of Copper Metal. Inorganic Chemistry, 2005, 44, 1728-1735.	1.9	151
46	Extending the Lifetime of Organic Flow Batteries via Redox State Management. Journal of the American Chemical Society, 2019, 141, 8014-8019.	6.6	151
47	Creation and Control of Two-Dimensional Electron Gas Using Al-Based Amorphous Oxides/SrTiO₃ Heterostructures Grown by Atomic Layer Deposition. Nano Letters, 2012, 12, 4775-4783.	4.5	149
48	Line Shapes in Molecular Spectra. Journal of Chemical Physics, 1968, 49, 2455-2456.	1.2	145
49	Improved Cu₂Oâ€Based Solar Cells Using Atomic Layer Deposition to Control the Cu Oxidation State at the pâ€n Junction. Advanced Energy Materials, 2014, 4, 1301916.	10.2	142
50	Calculation of Coefficients in the Power Series Expansion of the Longâ€Range Dispersion Force between Atoms. Journal of Chemical Physics, 1972, 56, 2801-2806.	1.2	138
51	Highly Conformal Thin Films of Tungsten Nitride Prepared by Atomic Layer Deposition from a Novel Precursor. Chemistry of Materials, 2003, 15, 2969-2976.	3.2	135
52	Diffusion barrier properties of tungsten nitride films grown by atomic layer deposition from bis(tert-butylimido)bis(dimethylamido)tungsten and ammonia. Applied Physics Letters, 2003, 82, 2239-2241.	1.5	135
53	Atomic Layer Deposition of Y2O3Thin Films from Yttrium Tris(N,Nâ€˜-diisopropylacetamidinate) and Water. Chemistry of Materials, 2005, 17, 4808-4814.	3.2	134
54	Coâ€optimization of SnS absorber and Zn(O,S) buffer materials for improved solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 901-908.	4.4	132

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55	Mapping the frontiers of quinone stability in aqueous media: implications for organic aqueous redox flow batteries. Journal of Materials Chemistry A, 2019, 7, 12833-12841.	5.2	128
56	Vapor Deposition of Metal Oxides and Silicates:â€‰ Possible Gate Insulators for Future Microelectronics. Chemistry of Materials, 2001, 13, 2463-2464.	3.2	126
57	Semiclassical approximations to 3jâ€•and 6jâ€coefficients for quantumâ€mechanical coupling of angular momenta. Journal of Mathematical Physics, 1975, 16, 1971-1988.	0.5	125
58	Low Temperature Atomic Layer Deposition of Tin Oxide. Chemistry of Materials, 2010, 22, 4964-4973.	3.2	121
59	On a semiclassical study of molecular collisions. I. General method. Journal of Chemical Physics, 1973, 58, 4131-4148.	1.2	118
60	Ionâ€ion interaction potentials and their application to the theory of alkali halide and alkaline earth dihalide molecules. Journal of Chemical Physics, 1974, 60, 4332-4344.	1.2	112
61	Near Neutral pH Redox Flow Battery with Low Permeability and Longâ€Lifetime Phosphonated Viologen Active Species. Advanced Energy Materials, 2020, 10, 2000100.	10.2	112
62	Chemical vapor deposition of coatings on glass. Journal of Non-Crystalline Solids, 1997, 218, 81-91.	1.5	109
63	Nitrogen-doped cuprous oxide as a p-type hole-transporting layer in thin-film solar cells. Journal of Materials Chemistry A, 2013, 1, 15416.	5.2	108
64	Nucleation and Adhesion of ALD Copper on Cobalt Adhesion Layers and Tungsten Nitride Diffusion Barriers. Electrochemical and Solid-State Letters, 2005, 8, G182.	2.2	105
65	Externally Assembled Gate-All-Around Carbon Nanotube Field-Effect Transistor. IEEE Electron Device Letters, 2008, 29, 183-185.	2.2	104
66	Semiclassical Perturbation Theory of Molecular Collisions. I. First and Second Order. Journal of Chemical Physics, 1970, 53, 1815-1831.	1.2	103
67	Glass-Encapsulated Light Harvesters: More Efficient Dye-Sensitized Solar Cells by Deposition of Self-Aligned, Conformal, and Self-Limited Silica Layers. Journal of the American Chemical Society, 2012, 134, 9537-9540.	6.6	103
68	Extremely Stable Anthraquinone Negolytes Synthesized from Common Precursors. CheM, 2020, 6, 1432-1442.	5.8	100
69	Atomic Layer Deposition of Insulating Hafnium and Zirconium Nitrides. Chemistry of Materials, 2004, 16, 3497-3501.	3.2	98
70	Tungsten Nitride Inverse Opals by Atomic Layer Deposition. Nano Letters, 2003, 3, 1293-1297.	4.5	97
71	A High Voltage Aqueous Zincâ€“Organic Hybrid Flow Battery. Advanced Energy Materials, 2019, 9, 1900694.	10.2	97
72	Band offsets of n-type electron-selective contacts on cuprous oxide (Cu2O) for photovoltaics. Applied Physics Letters, 2014, 105, .	1.5	96

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73	Molecular Engineering of an Alkaline Naphthoquinone Flow Battery. ACS Energy Letters, 2019, 4, 1880-1887.	8.8	90
74	Antimony-Doped Tin(II) Sulfide Thin Films. Chemistry of Materials, 2012, 24, 4556-4562.	3.2	88
75	Vibrational Relaxation of Diatomic Molecules in Gases and Liquids. Journal of Chemical Physics, 1967, 47, 1600-1608.	1.2	87
76	Ionâ€rare gas interactions on the repulsive part of the potential curves. Journal of Chemical Physics, 1974, 60, 4323-4331.	1.2	87
77	Calculations on the HClâ€“Ar van der Waals complex. Journal of Chemical Physics, 1976, 64, 354-363.	1.2	87
78	Textured tin oxide films produced by atmospheric pressure chemical vapor deposition from tetramethyltin and their usefulness in producing light trapping in thin film amorphous silicon solar cells. Solar Energy Materials and Solar Cells, 1989, 18, 263-281.	0.4	86
79	Three dimensional solid-state supercapacitors from aligned single-walled carbon nanotube array templates. Carbon, 2011, 49, 4890-4897.	5.4	84
80	Solution-phase reactivity as a guide to the low-temperature chemical vapor deposition of early-transition-metal nitride thin films. Journal of the American Chemical Society, 1990, 112, 7833-7835.	6.6	83
81	Error Bounds for the Longâ€Range Forces between Atoms. Journal of Chemical Physics, 1968, 48, 3929-3934.	1.2	82
82	Atomic layer deposited zinc tin oxide channel for amorphous oxide thin film transistors. Applied Physics Letters, 2012, 101, 113507.	1.5	82
83	Vapor Deposition of Ruthenium from an Amidinate Precursor. Journal of the Electrochemical Society, 2007, 154, D642.	1.3	81
84	In Situ Infrared Characterization during Atomic Layer Deposition of Lanthanum Oxide. Journal of Physical Chemistry C, 2009, 113, 654-660.	1.5	80
85	Symmetric All-Quinone Aqueous Battery. ACS Applied Energy Materials, 2019, 2, 4016-4021.	2.5	80
86	Properties of fluorine-doped tin oxide films produced by atmospheric pressure chemical vapor deposition from tetramethyltin, bromotrifluoromethane and oxygen. Thin Solid Films, 1992, 214, 175-187.	0.8	78
87	Atomic layer deposition of lanthanum aluminum oxide nano-laminates for electrical applications. Applied Physics Letters, 2004, 84, 3957-3959.	1.5	78
88	Band alignment of SnS/Zn(O,S) heterojunctions in SnS thin film solar cells. Applied Physics Letters, 2013, 103, 181904.	1.5	78
89	Surface Chemistry of Copper(I) Acetamidinates in Connection with Atomic Layer Deposition (ALD) Processes. Chemistry of Materials, 2011, 23, 3325-3334.	3.2	77
90	Bound atomâ€“diatomic molecule complexes. Anisotropic intermolecular potentials for the hydrogenâ€“rare gas systems. Journal of Chemical Physics, 1978, 68, 700-725.	1.2	76

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91	Heteroepitaxy of La2O3 and La2â€“xYxO3 on GaAs (111)A by Atomic Layer Deposition: Achieving Low Interface Trap Density. Nano Letters, 2013, 13, 594-599.	4.5	75
92	Surface and Interface Processes during Atomic Layer Deposition of Copper on Silicon Oxide. Langmuir, 2010, 26, 3911-3917.	1.6	73
93	pH swing cycle for CO₂capture electrochemically driven through proton-coupled electron transfer. Energy and Environmental Science, 2020, 13, 3706-3722.	15.6	73
94	Semiclassical Perturbation Theory of Molecular Collisions. II. The Calculation of Collision Cross Sections. Journal of Chemical Physics, 1970, 53, 1831-1850.	1.2	71
95	Tests of nonlocal kinetic energy functionals. Journal of Chemical Physics, 1994, 100, 4446-4452.	1.2	71
96	Deposition of Boron Doped Zinc Oxide Films and Their Electrical and Optical Properties. Journal of the Electrochemical Society, 1992, 139, 2014-2022.	1.3	69
97	Synthesis of N-Heterocyclic Stannylene (Sn(II)) and Germylene (Ge(II)) and a Sn(II) Amidinate and Their Application as Precursors for Atomic Layer Deposition. Chemistry of Materials, 2014, 26, 3065-3073.	3.2	69
98	Preparation and Properties of Transparent Conductors. Materials Research Society Symposia Proceedings, 1996, 426, 419.	0.1	67
99	Selective Chemical Vapor Deposition of Manganese Self-Aligned Capping Layer for Cu Interconnections in Microelectronics. Journal of the Electrochemical Society, 2010, 157, D341.	1.3	67
100	Atmospheric pressure chemical vapor deposition of transparent conducting films of fluorine doped zinc oxide and their application to amorphous silicon solar cells. Journal of Materials Science, 2007, 42, 6388-6399.	1.7	66
101	Gasâ€phase kinetics in the atmospheric pressure chemical vapor deposition of silicon from silane and disilane. Journal of Applied Physics, 1990, 67, 1062-1075.	1.1	65
102	Atmospheric Pressure Chemical Vapor Deposition of Titanium Nitride from Tetrakis (diethylamido) Titanium and Ammonia. Journal of the Electrochemical Society, 1996, 143, 736-744.	1.3	64
103	Highly conformal atomic layer deposition of tantalum oxide using alkylamide precursors. Thin Solid Films, 2003, 443, 1-4.	0.8	64
104	Intermolecular Potentials and Infrared Spectra. Journal of Chemical Physics, 1971, 55, 4898-4906.	1.2	63
105	ALD of High-Îº Dielectrics on Suspended Functionalized SWNTs. Electrochemical and Solid-State Letters, 2005, 8, G89.	2.2	62
106	Direct-Liquid-Injection Chemical Vapor Deposition of Nickel Nitride Films and Their Reduction to Nickel Films. Chemistry of Materials, 2010, 22, 3060-3066.	3.2	61
107	Quantum theory of angular momentum coupling in reactive collisions. Journal of Chemical Physics, 1976, 64, 2918-2938.	1.2	60
108	Thin, Continuous, and Conformal Copper Films by Reduction of Atomic Layer Deposited Copper Nitride. Chemical Vapor Deposition, 2006, 12, 435-441.	1.4	59

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109	High density Ru nanocrystal deposition for nonvolatile memory applications. Journal of Applied Physics, 2007, 101, 124503.	1.1	58
110	Atomic layer deposition of insulating nitride interfacial layers for germanium metal oxide semiconductor field effect transistors with high-Î¹ oxide/tungsten nitride gate stacks. Applied Physics Letters, 2007, 90, 212104.	1.5	58
111	Atmospheric pressure chemical vapor deposition of TiN from tetrakis(dimethylamido)titanium and ammonia. Journal of Materials Research, 1996, 11, 989-1001.	1.2	57
112	Tantalum(V) Nitride Inverse Opals as Photonic Structures for Visible Wavelengths. Journal of Physical Chemistry B, 2005, 109, 3764-3771.	1.2	57
113	UV-Vis spectrophotometry of quinone flow battery electrolyte for in situ monitoring and improved electrochemical modeling of potential and quinhydrone formation. Physical Chemistry Chemical Physics, 2017, 19, 31684-31691.	1.3	57
114	In situ electrochemical recomposition of decomposed redox-active species in aqueous organic flow batteries. Nature Chemistry, 2022, 14, 1103-1109.	6.6	55
115	Accurate analytic approximations for the rotating Morse oscillator: Energies, wave functions, and matrix elements. Journal of Chemical Physics, 1982, 76, 5452-5457.	1.2	54
116	Atomic layer deposition of gadolinium scandate films with high dielectric constant and low leakage current. Applied Physics Letters, 2006, 89, 133512.	1.5	54
117	Synthesis and characterization of volatile liquid cobalt amidinates. Dalton Transactions, 2008, , 2592.	1.6	52
118	Uptake of Copper Acetamidinate ALD Precursors on Nickel Surfaces. Chemistry of Materials, 2010, 22, 352-359.	3.2	51
119	Filling Narrow Trenches by Iodine-Catalyzed CVD of Copper and Manganese on Manganese Nitride Barrier/Adhesion Layers. Journal of the Electrochemical Society, 2011, 158, D248.	1.3	51
120	Local asymptotic gradient corrections to the energy functional of an electron gas. Journal of Chemical Physics, 1985, 82, 881-889.	1.2	49
121	Size-Dependent-Transport Study of $hbox{In}_{0.53} hbox{Ga}_{0.47}hbox{As}$ Gate-All-Around Nanowire MOSFETs: Impact of Quantum Confinement and Volume Inversion. IEEE Electron Device Letters, 2012, 33, 967-969.	2.2	49
122	A kinematic, classical mechanical theory of reactive collisions. Journal of Chemical Physics, 1982, 76, 3009-3018.	1.2	47
123	Kinetic Modeling of the Chemical Vapor Deposition of Silicon Dioxide from Silane or Disilane and Nitrous Oxide. Journal of the Electrochemical Society, 1990, 137, 3237-3253.	1.3	47
124	Sealing Porous Low-k Dielectrics with Silica. Electrochemical and Solid-State Letters, 2004, 7, G306.	2.2	47
125	Transient terahertz photoconductivity measurements of minority-carrier lifetime in tin sulfide thin films: Advanced metrology for an early stage photovoltaic material. Journal of Applied Physics, 2016, 119, .	1.1	47
126	Generalized electron gasâ€“Drude model theory of intermolecular forces. Journal of Chemical Physics, 1979, 71, 1340-1352.	1.2	46

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127	High-Performance InAlN/GaN MOSHEMTs Enabled by Atomic Layer Epitaxy MgCaO as Gate Dielectric. IEEE Electron Device Letters, 2016, 37, 556-559.	2.2	46
128	Novel phase diagram behavior and materials design in heterostructural semiconductor alloys. Science Advances, 2017, 3, e1700270.	4.7	46
129	Atomic layer deposition of tin oxide with nitric oxide as an oxidant gas. Journal of Materials Chemistry, 2012, 22, 4599.	6.7	44
130	Atmospheric pressure chemical vapor deposition of aluminum nitride thin films at 200â€“250 Â°C. Journal of Materials Research, 1991, 6, 5-7.	1.2	41
131	Chemical vapor deposition of aluminum nitride thin films. Journal of Materials Research, 1992, 7, 1679-1684.	1.2	41
132	Atomic Layer Deposition of Lanthanum-Based Ternary Oxides. Electrochemical and Solid-State Letters, 2009, 12, G13.	2.2	40
133	Heteroepitaxy of single-crystal LaLuO3 on GaAs(111)A by atomic layer deposition. Applied Physics Letters, 2010, 97, 162910.	1.5	39
134	Atomic layer deposition of Sc2O3 for passivating AlGaN/GaN high electron mobility transistor devices. Applied Physics Letters, 2012, 101, 232109.	1.5	39
135	Atomic layer deposition of Zn(O,S) thin films with tunable electrical properties by oxygen annealing. Applied Physics Letters, 2013, 102, .	1.5	39
136	Effect of Molecular Structure of Quinones and Carbon Electrode Surfaces on the Interfacial Electron Transfer Process. ACS Applied Energy Materials, 2020, 3, 1933-1943.	2.5	38
137	Alkaline Quinone Flow Battery with Long Lifetime at pH 12. Joule, 2018, 2, 1907-1908.	11.7	37
138	Functioning Waterâ€Insoluble Ferrocenes for Aqueous Organic Flow Battery via Hostâ€“Guest Inclusion. ChemSusChem, 2021, 14, 745-752.	3.6	37
139	Modulated Double Resonance and Inelastic Collisions. Journal of Chemical Physics, 1967, 46, 4399-4403.	1.2	36
140	ALD of Scandium Oxide from Scandium Tris(N,N[sup Ê¹]-diisopropylacetamidinate) and Water. Electrochemical and Solid-State Letters, 2006, 9, F45.	2.2	36
141	High-performance anthraquinone with potentially low cost for aqueous redox flow batteries. Journal of Materials Chemistry A, 2021, 9, 26709-26716.	5.2	36
142	Exact Solutions to the Coupled Hartreeâ€Fock Perturbation Equations. Journal of Chemical Physics, 1972, 56, 3823-3831.	1.2	35
143	Anthraquinone Flow Battery Reactants with Nonhydrolyzable Water-Solubilizing Chains Introduced via a Generic Cross-Coupling Method. ACS Energy Letters, 2022, 7, 226-235.	8.8	35
144	Vapor Deposition of Highly Conformal Copper Seed Layers for Plating Through-Silicon Vias (TSVs). Journal of the Electrochemical Society, 2012, 159, D382-D385.	1.3	34

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145	Constructing Wavefunctions for Nonlocal Potentials. Journal of Chemical Physics, 1970, 52, 6211-6217.	1.2	32
146	Solution for bound state wavefunctions and matrix elements by the piecewise analytic method. Journal of Chemical Physics, 1976, 64, 4984-4994.	1.2	32
147	Chemical Vapor Deposition of Cobalt Nitride and its Application as an Adhesion-Enhancing Layer for Advanced Copper Interconnects. ECS Journal of Solid State Science and Technology, 2012, 1, N79-N84.	0.9	32
148	Molecular inelastic neutron scattering: Computational methods using consistent force fields. Journal of Chemical Physics, 1974, 61, 2929-2939.	1.2	31
149	Titanium Nitride Thin Films: Properties and Apcvd Synthesis Using Organometallic Precursors. Materials Research Society Symposia Proceedings, 1989, 168, 357.	0.1	31
150	A Long Lifetime Aqueous Organic Solar Flow Battery. Advanced Energy Materials, 2019, 9, 1900918.	10.2	31
151	Bounded error analysis of experimental distributions of relaxation times. Journal of Chemical Physics, 1979, 71, 1159-1166.	1.2	30
152	Simple method for preparing hydrogenated amorphous silicon films by chemical vapor deposition at atmospheric pressure. Journal of Applied Physics, 1983, 54, 5381-5384.	1.1	30
153	Ultrathin CVD Cu Seed Layer Formation Using Copper Oxynitride Deposition and Room Temperature Remote Hydrogen Plasma Reduction. Journal of the Electrochemical Society, 2008, 155, H496.	1.3	30
154	Epitaxial Growth of Mg_xCa_{1â€“x}O on GaN by Atomic Layer Deposition. Nano Letters, 2016, 16, 7650-7654.	4.5	30
155	Flow Batteries: Alkaline Benzoquinone Aqueous Flow Battery for Largeâ€Scale Storage of Electrical Energy (Adv. Energy Mater. 8/2018). Advanced Energy Materials, 2018, 8, 1870034.	10.2	30
156	Atomic Layer Deposition of Praseodymium Aluminum Oxide for Electrical Applications. Chemical Vapor Deposition, 2006, 12, 152-157.	1.4	29
157	(Sn,Al)O_x Films Grown by Atomic Layer Deposition. Journal of Physical Chemistry C, 2011, 115, 10277-10283.	1.5	29
158	Framework to predict optimal buffer layer pairing for thin film solar cell absorbers: A case study for tin sulfide/zinc oxysulfide. Journal of Applied Physics, 2015, 118, .	1.1	29
159	Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. Angewandte Chemie - International Edition, 2016, 55, 10228-10233.	7.2	29
160	Enhancement of the open circuit voltage of Cu2O/Ga2O3 heterojunction solar cells through the mitigation of interfacial recombination. AIP Advances, 2019, 9, .	0.6	29
161	In situelectrosynthesis of anthraquinone electrolytes in aqueous flow batteries. Green Chemistry, 2020, 22, 6084-6092.	4.6	29
162	Thermal chemistry of copper(I)-N,Nâ€‰â€²-di-sec-butylacetamidinate on Cu(110) single-crystal surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	28

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163	Synthesis of vanadium dioxide thin films on conducting oxides and metalâ€“insulator transition characteristics. Journal of Crystal Growth, 2012, 338, 96-102.	0.7	28
164	Obtaining a Low and Wide Atomic Layer Deposition Window (150â€“275â€‰Â°C) for In₂O₃ Films Using an In^{III} Amidinate and H₂O. Chemistry - A European Journal, 2018, 24, 9525-9529.	1.7	28
165	A Kinetics Study of the Atmospheric Pressure CVD Reaction of Silane and Nitrous Oxide. Journal of the Electrochemical Society, 1989, 136, 2993-3003.	1.3	27
166	Computational Study on the Relative Reactivities of Cobalt and Nickel Amidinates via Î²-H Migration. Organometallics, 2007, 26, 2803-2805.	1.1	27
167	DC and RF Performance of AlGaN/GaN/SiC MOSHEMTs With Deep Sub-Micron T-Gates and Atomic Layer Epitaxy MgCaO as Gate Dielectric. IEEE Electron Device Letters, 2017, 38, 1409-1412.	2.2	27
168	Generalized electron gasâ€“Drude model theory for ionâ€“molecule forces. Journal of Chemical Physics, 1979, 71, 1353-1358.	1.2	26
169	ALD Precursors and Reaction Mechanisms. , 2014, , 15-46.		26
170	Low Temperature Chemical Vapor Deposition of Cuprous Oxide Thin Films Using a Copper(I) Amidinate Precursor. ACS Applied Energy Materials, 2019, 2, 7750-7756.	2.5	26
171	Quantum colinear inelastic and reactive scattering with piecewise analytic wavefunctions. Journal of Chemical Physics, 1976, 64, 1641-1658.	1.2	25
172	Electronâ€gas model for open shellâ€“closed shell interactions. I. Application to the emission spectra of the diatomic nobleâ€gas halides. Journal of Chemical Physics, 1977, 66, 239-243.	1.2	25
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